



High Performance Grating-Outcoupled Surface Emitting(GSE) Lasers Using Quantum Well Intermixing

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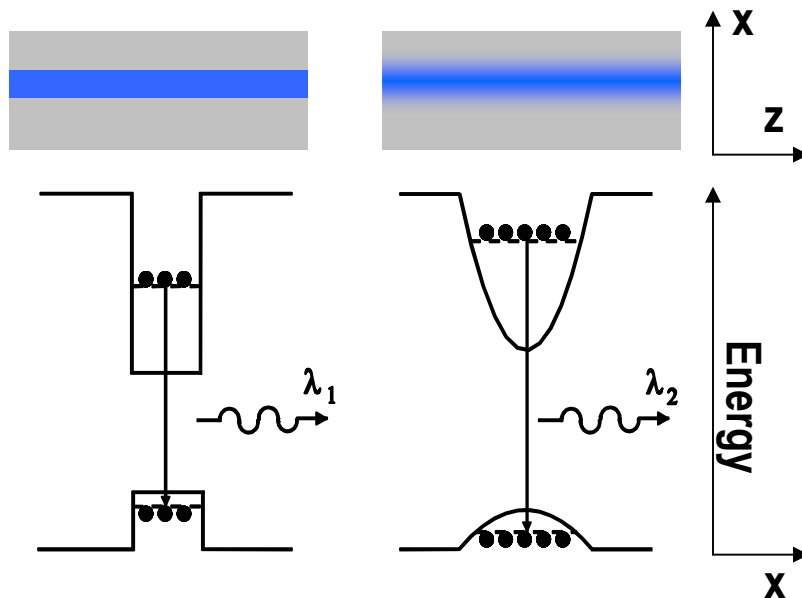
June 25th, 2004



Agilent Technologies

A Collaboration with Photodigm Inc. and Agilent Technologies

Quantum Well Intermixing (QWI)



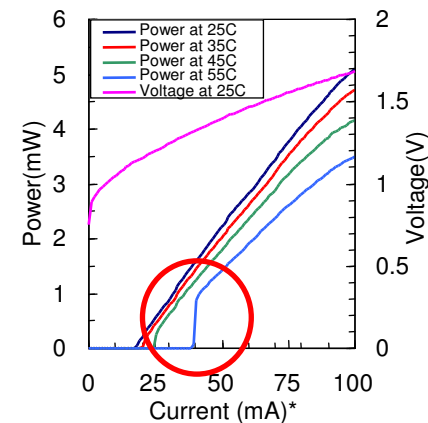
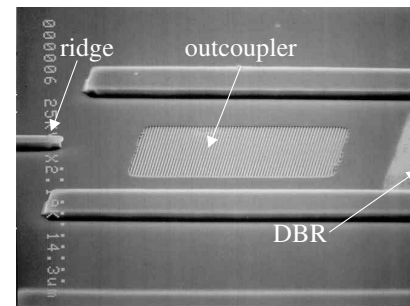
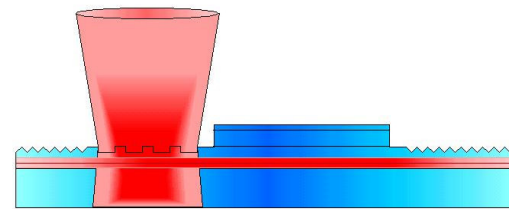
- Applications:
 - Multi-wavelength laser arrays
 - Quantum well lasers
 - Waveguide demultiplexer
 - Photodetectors
 - Modulators
- Our Interests
 - GSE lasers
 - Multi-wavelength cross-grating GSE lasers



Grating-outcoupled Surface Emitting (GSE) lasers

- 1st order feedback grating + 2nd order outcoupler grating
- Problem: “snap-on” behavior at high temperature due to a combination of low DBR reflectivity and the saturated absorption of the quantum wells in the passive DBR and outcoupler regions.
- Solutions:
 - Increasing DBR reflectivity
 - Quantum Well Intermixing in passive DBR and outcoupler sections
- Perspective:
 - Lower threshold (10 mA)
 - Higher slope efficiency (0.2 W/A)
 - Higher temperature operation (>100C)
 - Higher modulation speed (> 5 Gbps)
 - No “snap-on” behavior

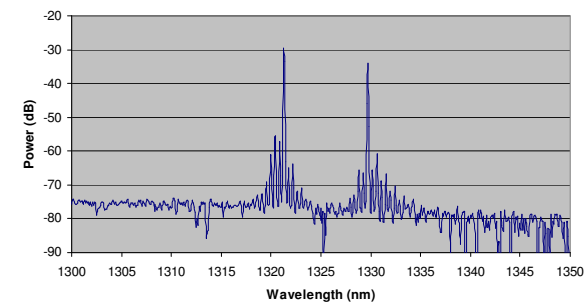
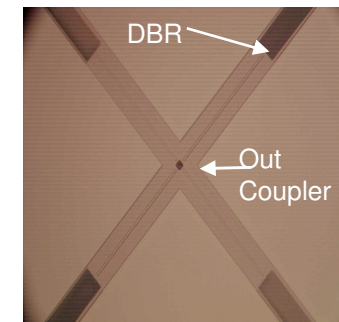
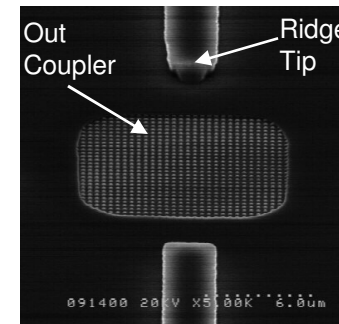
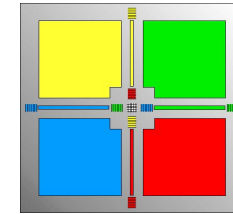
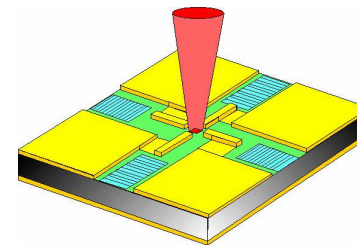
* Data provided by Photodigm Inc.



Multi-Wavelength Cross-Grating GSE Lasers

- **Monolithic multi-wavelength optical sources:**
 - WDM: 0.8 nm spacing
 - CWDM: 20 nm spacing
- **Current 2-wavelength Cross Grating GSE:**
 - 8 nm spacing
 - > 0.5 mW output power
- **Using QWI:**
 - Higher power, lower threshold
 - 20 nm spacing for CWDM application
- **Future goal: 4 wavelengths emitting from one single aperture**
 - Cover 80 nm wavelength range

* Data provided by Photodigm Inc.



Research Plan

Phase I

- Experiment ion implantation approach to develop processes of selective intermixing without severe PL intensity saturation.
- Fabricate ridge waveguide lasers from the GSE wafer structure using QWI.

Phase II

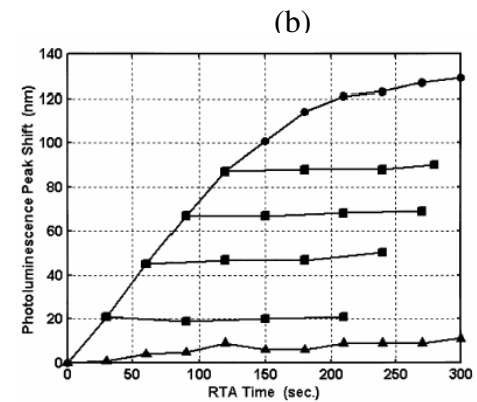
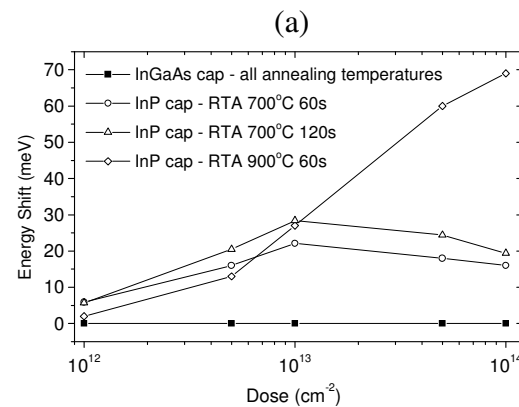
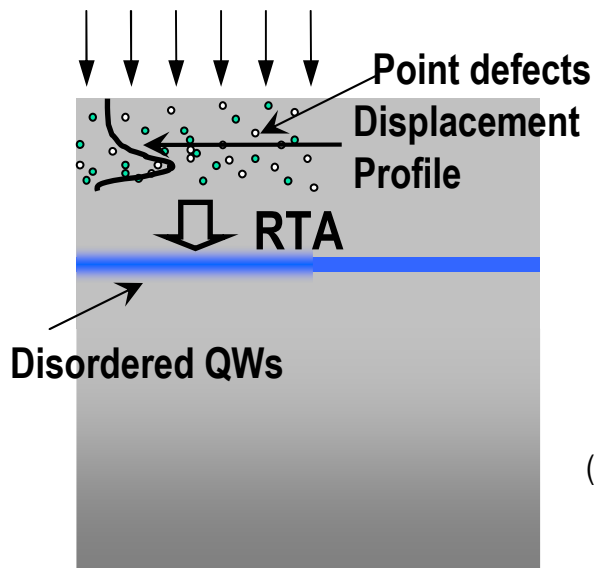
- Develop QWI processes for GSE lasers to improve their performances.
- Investigate the reproducibility of the processes.

Phase III

- Apply QWI to the active regions of GSE lasers to modify the lasing wavelengths.
- Develop GSE Laser arrays with multiple lasing wavelengths using QWI.



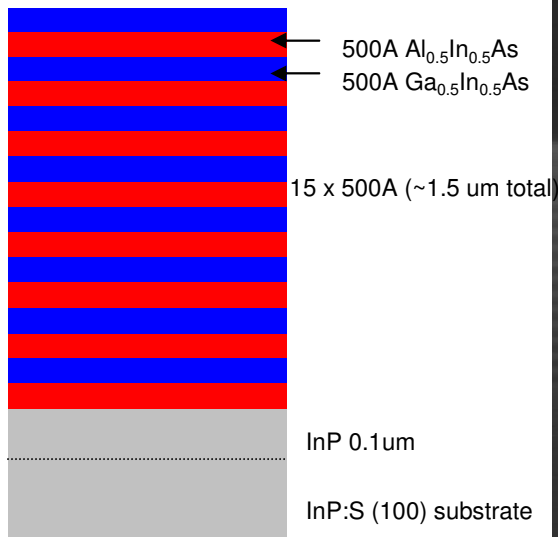
QWI by Ion Implantation



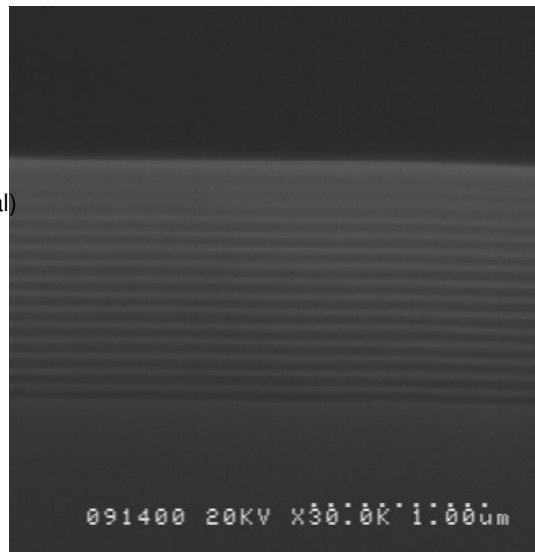
- (a) Energy shifts of InGaAs/AlGaInAs quantum wells as a function of dose for 20 keV P ion cap implants at 25C for different annealing temperatures and cap layers. (Carmody (2003), Defect Engineering of InP and InGaAs for Optoelectronic Applications, PhD thesis, Canberra, Australian National University)
- (b) PL wavelength peak shift as a function of anneal time for InGaAsP MQW. (Skogen et al., Journal of Quantum Electronics, Vol. 9, No. 5,p1183 – 1190 (2003))

QWI Experiment Results (1)

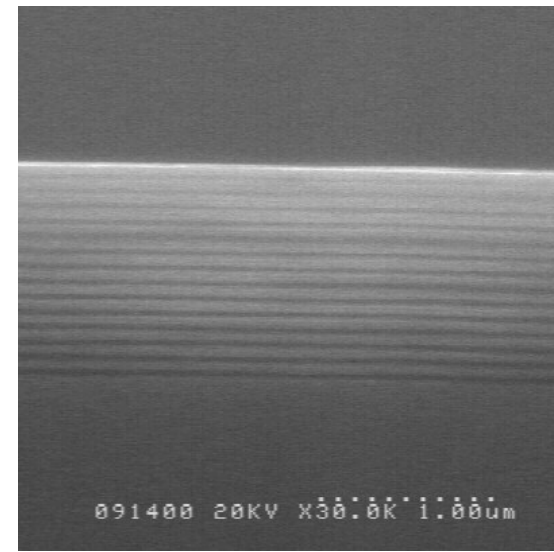
Super Lattice Structure



SEM picture before RTA

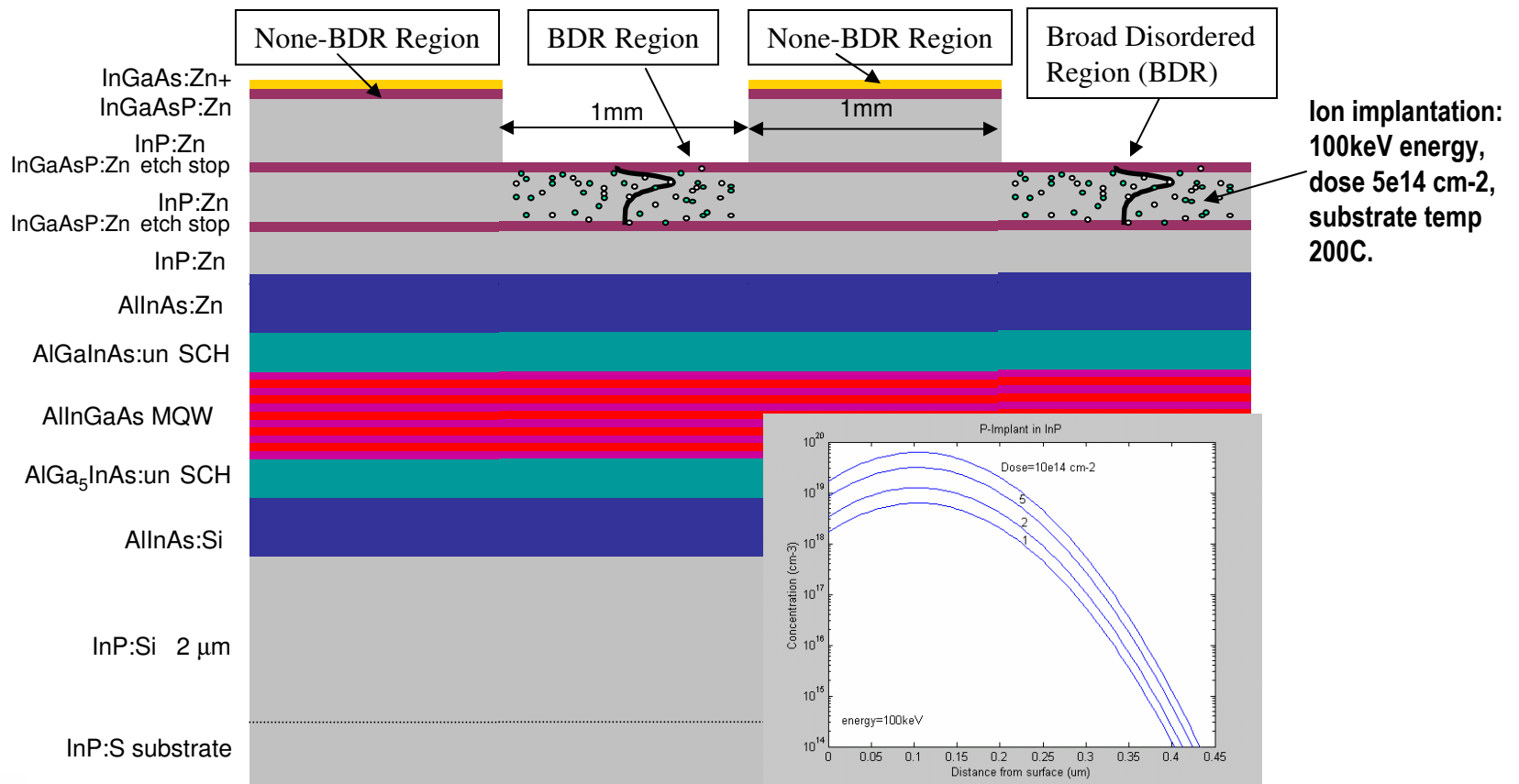


SEM picture after RTA at 700 C for 10 mins



OMLW 2572 A-A (AllnAs on surface)

Wafer Structures for QWI Experiments (2)



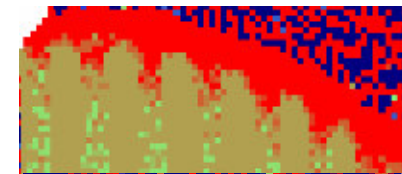
Summary of Experimental Data

Summary of wavelength shifts of wafer 2709B-A after QWI

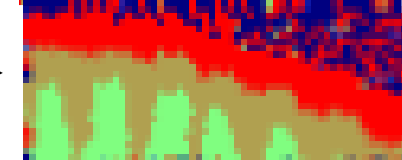
RTA @ 675C Time	Wavelength shift (nm) in BDR (broad disorder region) (Total 9 channels)				
	7-1	7-2	7-3	7-4	8-1
2min	8.6	8.6	8.6	8.6	8.6
10 min	8.5	8.5	8.5	8.5	0
Total shift for 12 mins	17.1	17.1	17.1	17.1	8.6

PL Spectrum Maps of 2709B-A

1. Before RTA →



2. After RTA at 675C for 2 mins →



3. After another RTA at 675C for 10 mins

